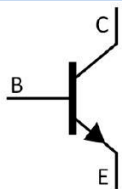


SOT-23 NPN Silicon NPN transistor in a SOT-23 Plastic Package.

2SA1036K
 Large I_C , low $V_{CE(sat)}$, complementary pair with the 2SA1036K.

Medium power amplifier applications.



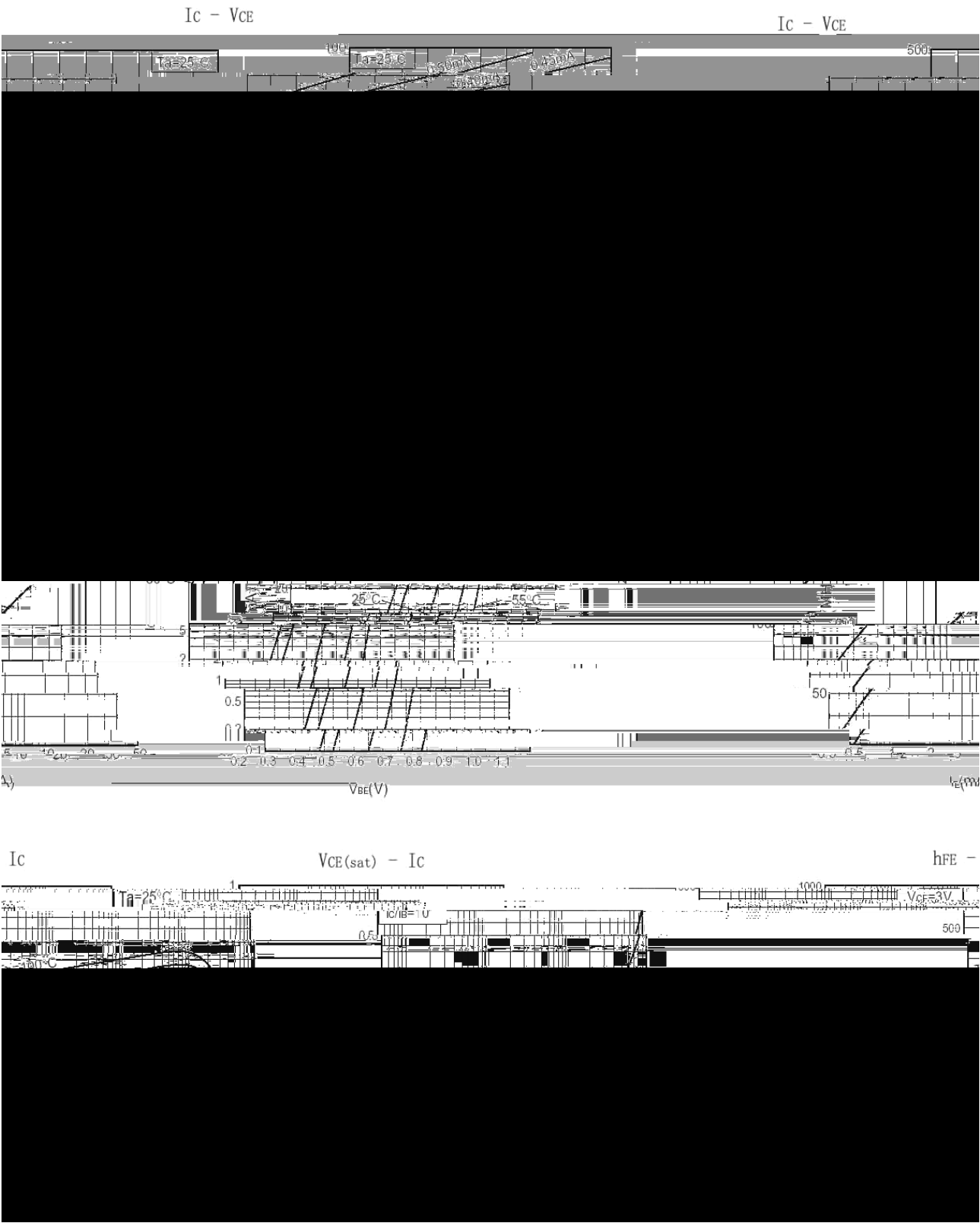
PIN1 Base PIN 2 Emitter PIN 3 Collector

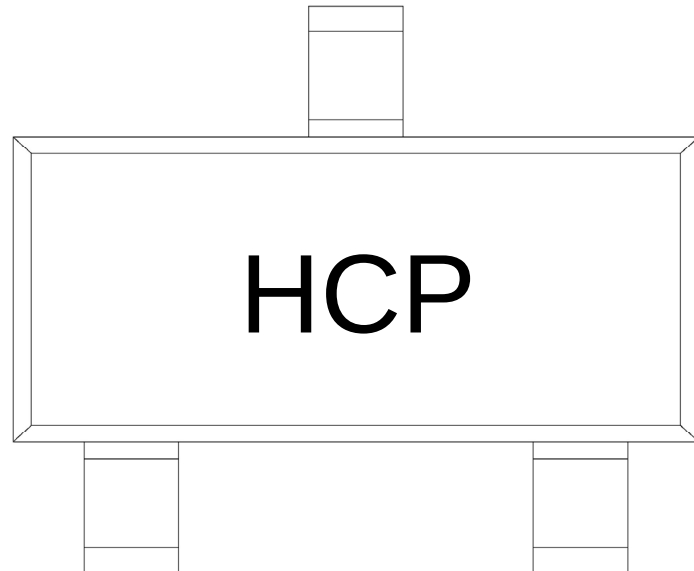
h_{FE} Classifications Symbol	P	Q	R
h_{FE} Range	82 180	120 270	180 390
Marking	HCP	HCQ	HCR

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	32	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	500	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- Base Breakdown Voltage	V_{CBO}	$I_C = 100 \text{ A}$	40			V
Collector-Emitter Breakdown Voltage	V_{CEO}	$I_C = 1.0 \text{ mA}$	32			V
Emitter-Base Breakdown Voltage	V_{EBO}	$I_E = 100 \text{ A}$	5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = 20 \text{ V}$			1.0	A
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB} = 4.0 \text{ V}$			1.0	A
DC Current Gain	h_{FE}	$V_{CE} = 3.0 \text{ V}$ $I_C = 10 \text{ mA}$	82		390	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 100 \text{ mA}$ $I_B = 1.0 \text{ mA}$			0.4	V

Tf57.0 10.5 268.02 358.2803 Tm0 Tc(V)Tj7.02 0 0 7.02 275.04 356.7803.0031 Tw(T)31m-0.06(f1 Tw[TH.5 57.66 29





H

C

P

h_{FE}

Note:

H

Company Code

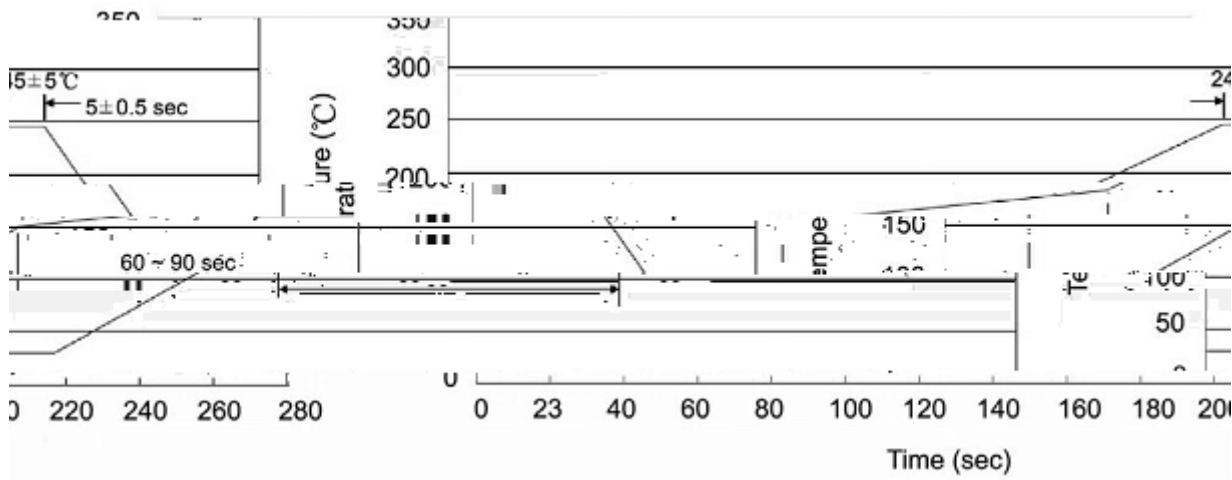
C

Product Type Code

P

h_{FE} Classifications Symbol Code

Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;

1.Preheating:25~150 , Time:60~90sec.
- 2

245±5

5±0.5sec;

2.Peak Temp.:245±5 , Duration:5±0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT-23	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205